



# STL10N3LLH5

N-channel 30 V, 0.015  $\Omega$ , 9 A, PowerFLAT™ 3.3x3.3  
STripFET™ V Power MOSFET

## Features

Order code	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STL10N3LLH5	30 V	< 0.019 $\Omega$	9 A <sup>(1)</sup>

1. The value is rated according Rthj-pcb

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- Very low switching gate charge
- High avalanche ruggedness
- Low gate drive power losses

## Applications

- Switching applications
- Automotive

## Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™ V technology. The device has been optimized to achieve very low on-state resistance, contributing to an FOM that is among the best in its class.

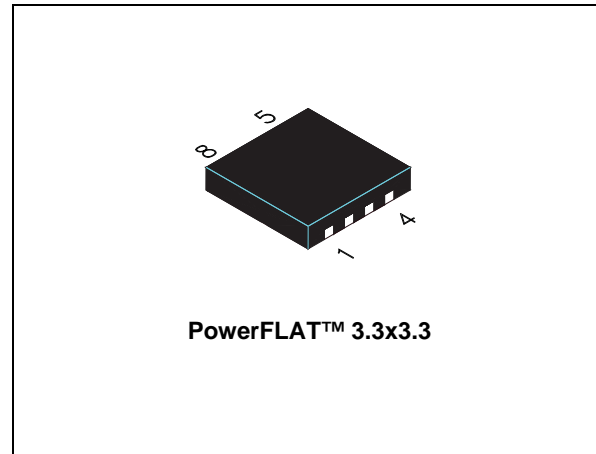


Figure 1. Internal schematic diagram

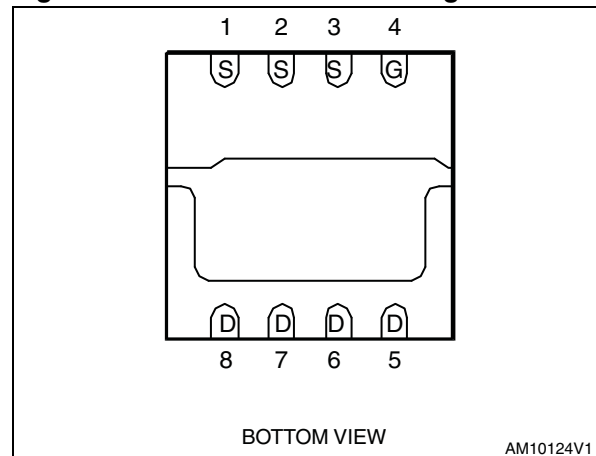


Table 1. Device summary

Order code	Marking	Package	Packaging
STL10N3LLH5	10N3L	PowerFLAT™ 3.3x3.3	Tape and reel

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 22$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	9	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6	A
$I_{DM}^{(2)}$	Drain current (pulsed)	36	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	50	W
	Derating factor	0.4	W/ $^\circ\text{C}$
$P_{TOT}^{(1)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	2	W
	Derating factor	0.02	W/ $^\circ\text{C}$
$T_J$ $T_{stg}$	Operating junction temperature storage temperature	-55 to 150	$^\circ\text{C}$

1. The value is rated according  $R_{thj-pcb}$
2. Pulse width limited by safe operating area.

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	42.8	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb (steady state)	62.5	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch<sup>2</sup>, 2oz Cu,  $t < 10\text{sec}$

**Table 4. Avalanche data**

Symbol	Parameter	Value	Unit
$I_{AV}^{(1)}$	Not-repetitive avalanche current	7.5	A
$E_{AS}^{(2)}$	Thermal resistance junction-pcb	150	mJ

1. Pulse width limited by  $T_{Jmax}$ .
2. Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AV}$ ,  $V_{DD} = 21\text{ V}$

## 2 Electrical characteristics

( $T_{CASE}=25\text{ }^{\circ}\text{C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ( $V_{GS}=0$ )	$I_D = 250\text{ }\mu\text{A}$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS}=0$ )	$V_{DS} = 30\text{ V}$ , $V_{DS} = 30\text{ V}$ , $T_C = 125\text{ }^{\circ}\text{C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS}=0$ )	$V_{GS} = \pm 22\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS}=10\text{ V}$ , $I_D=4.5\text{ A}$ $V_{GS}=4.5\text{ V}$ , $I_D=4.5\text{ A}$		15 19	19 22	$\text{m}\Omega$ $\text{m}\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS}=25\text{ V}$ , $f=1\text{ MHz}$ , $V_{GS}=0$	-	724	900 <sup>(1)</sup>	pF
$C_{oss}$	Output capacitance			132	165 <sup>(1)</sup>	pF
$C_{rss}$	Reverse transfer capacitance			20	25 <sup>(1)</sup>	pF
$Q_g$	Total gate charge	$V_{DD}=15\text{ V}$ , $I_D = 9\text{ A}$	-	5	6 <sup>(1)</sup>	nC
$Q_{gs}$	Gate-source charge	$V_{GS}=4.5\text{ V}$		2	2.5 <sup>(1)</sup>	nC
$Q_{gd}$	Gate-drain charge	(see Figure 14)		2	2.5 <sup>(1)</sup>	nC
$R_G$	Gate input resistance	$f=1\text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV Open drain	-		3.3	$\Omega$

1. Max values not tested

**Table 7. Switching times<sup>(1)</sup>**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=15\text{ V}$ , $I_D=4.5\text{ A}$ , $R_G=4.7\text{ }\Omega$ , $V_{GS}=10\text{ V}$ (see Figure 13)	-	4	5	ns
$t_r$	Rise time			4.2	5.2	ns
$t_{d(off)}$	Turn-off delay time			21	26	ns
$t_f$	Fall time			3.5	4.25	ns

1. Max values not tested

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=9\text{ A}$ , $V_{GS}=0$	-		1.1	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=20\text{ V}$ , $T_j=150\text{ }^\circ\text{C}$ <i>(see Figure 18)</i>	-	21 10 1		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

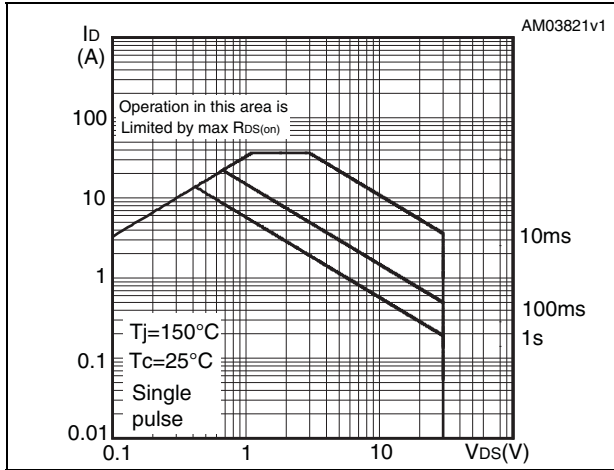


Figure 3. Thermal impedance

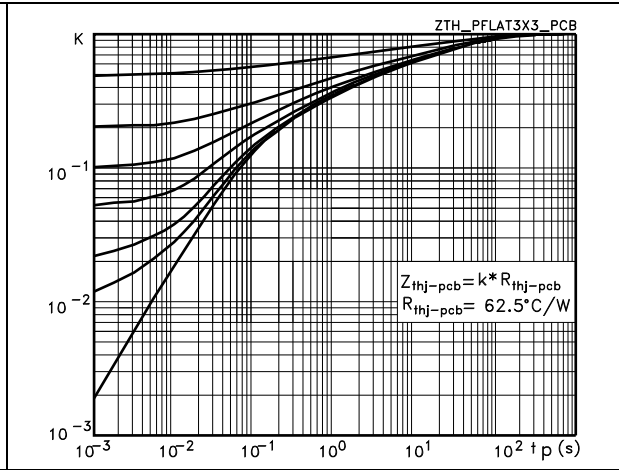


Figure 4. Output characteristics

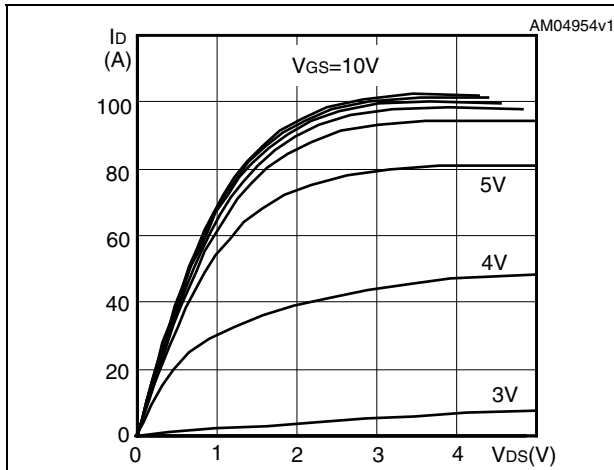


Figure 5. Transfer characteristics

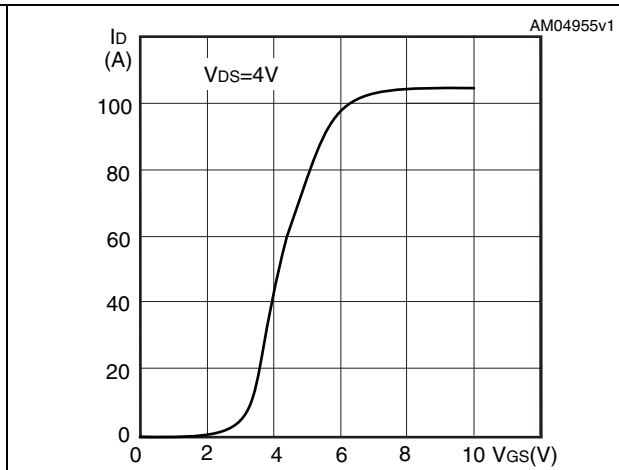


Figure 6. Normalized  $B_{V_{DSS}}$  vs temperature

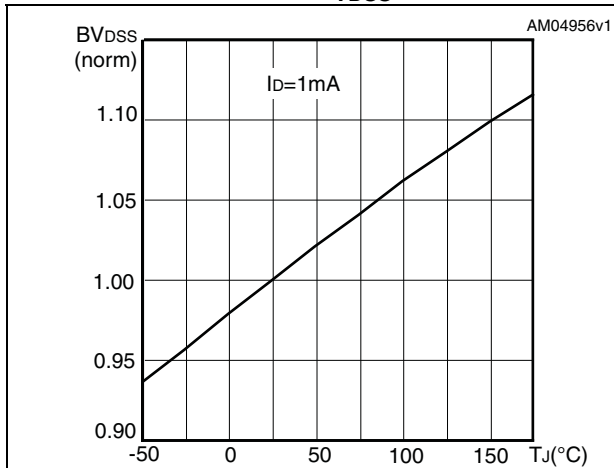
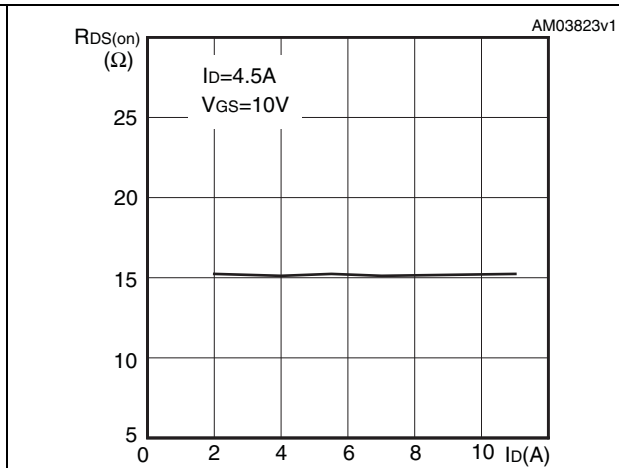
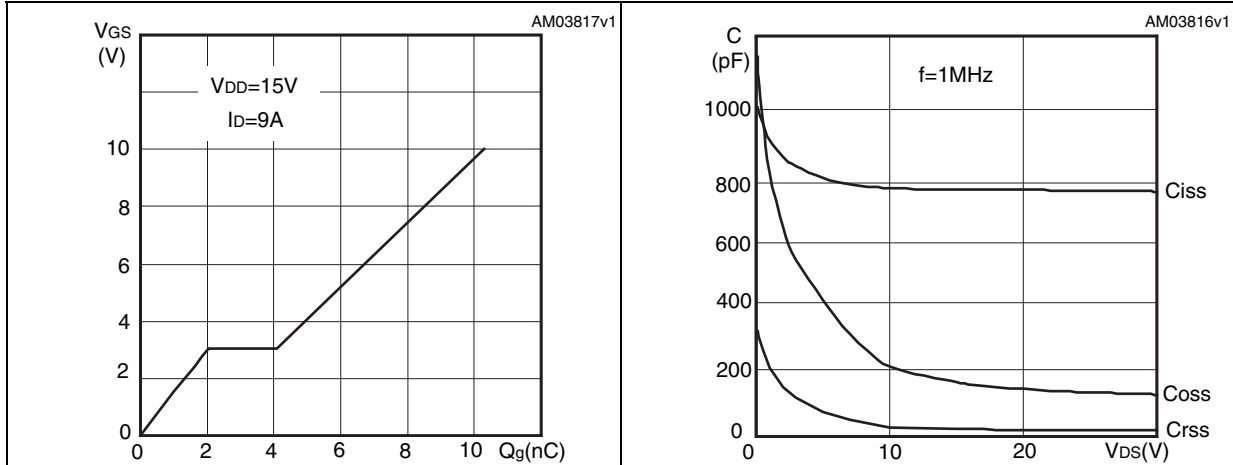


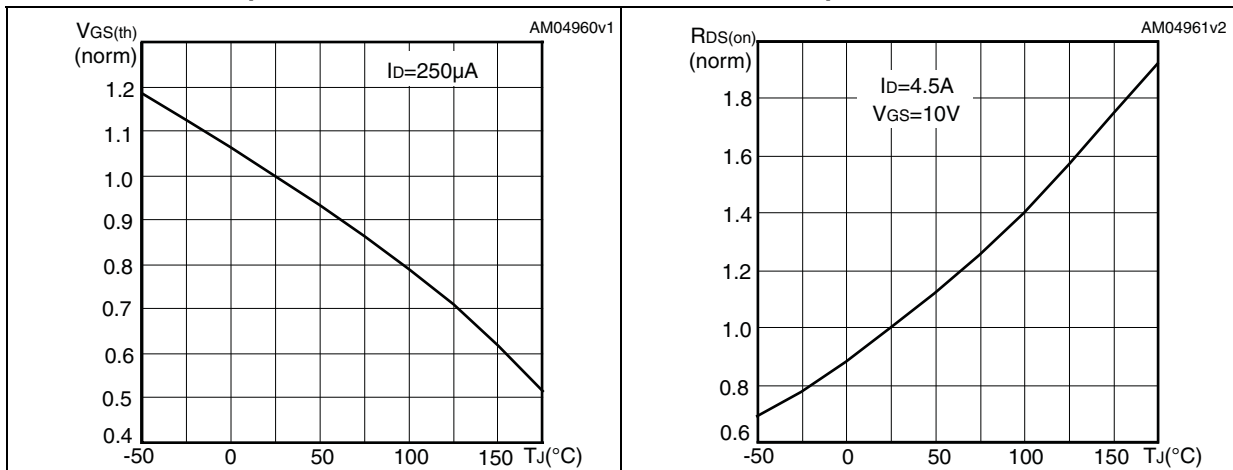
Figure 7. Static drain-source on resistance



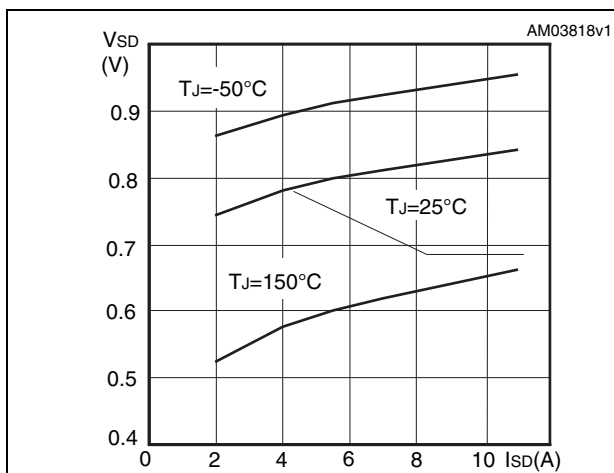
**Figure 8. Gate charge vs gate-source voltage** **Figure 9. Capacitance variations**



**Figure 10. Normalized gate threshold voltage vs temperature** **Figure 11. Normalized on resistance vs temperature**

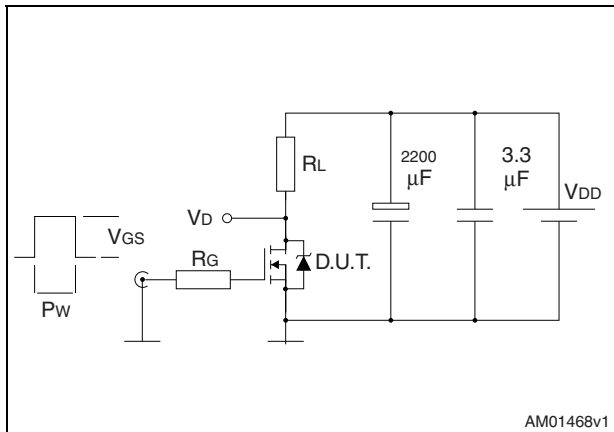


**Figure 12. Source-drain diode forward characteristics**



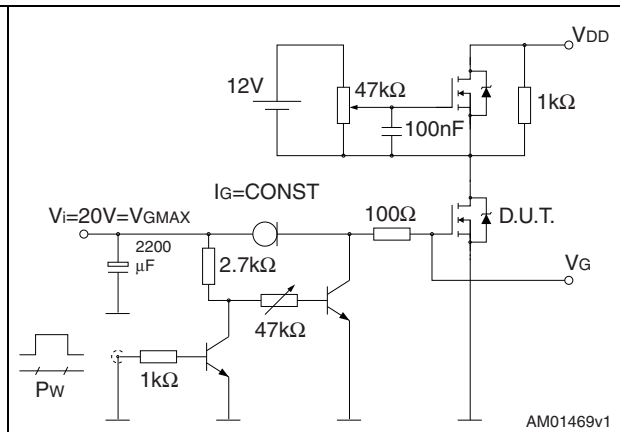
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



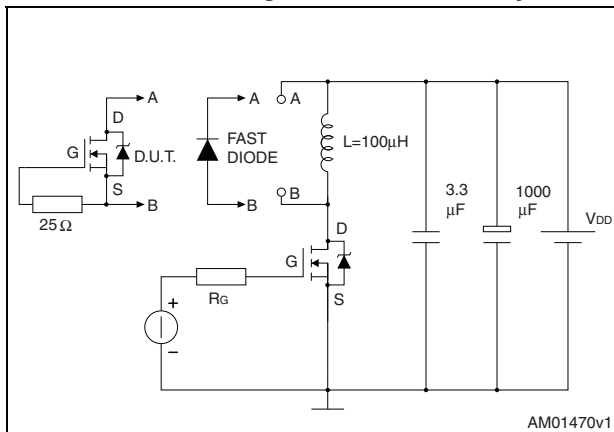
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**Figure 14. Gate charge test circuit**



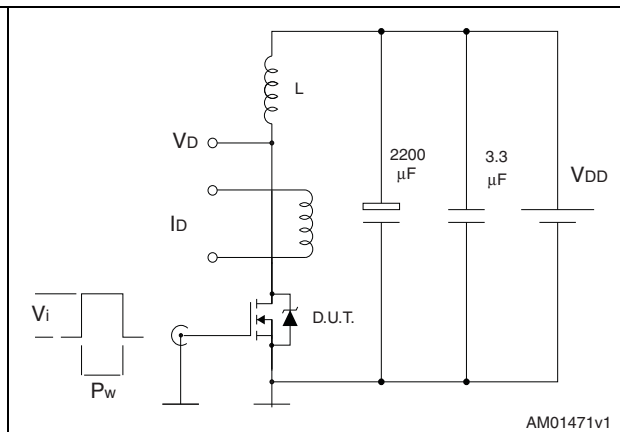
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**Figure 15. Test circuit for inductive load switching and diode recovery times**



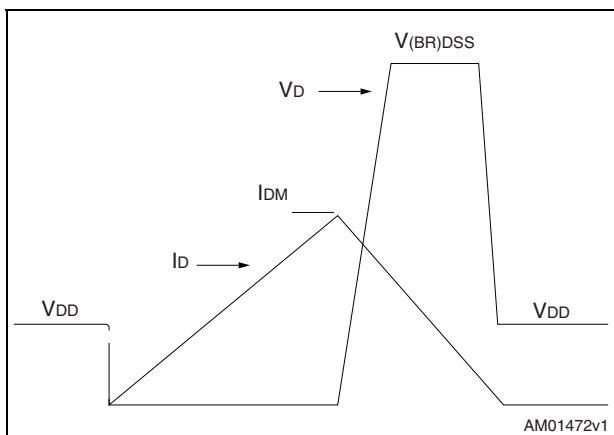
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**Figure 16. Unclamped inductive load test circuit**



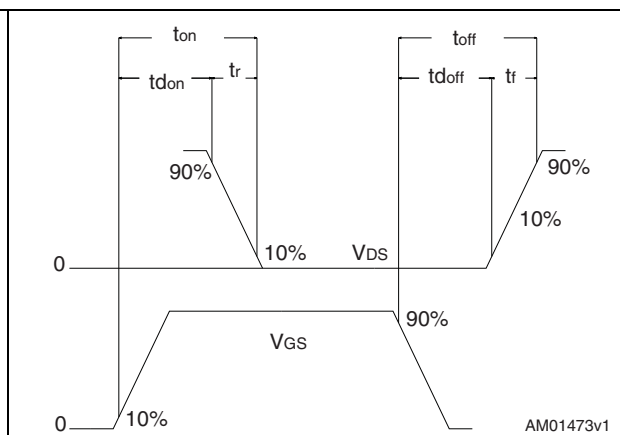
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**Figure 17. Unclamped inductive waveform**



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**Figure 18. Switching time waveform**



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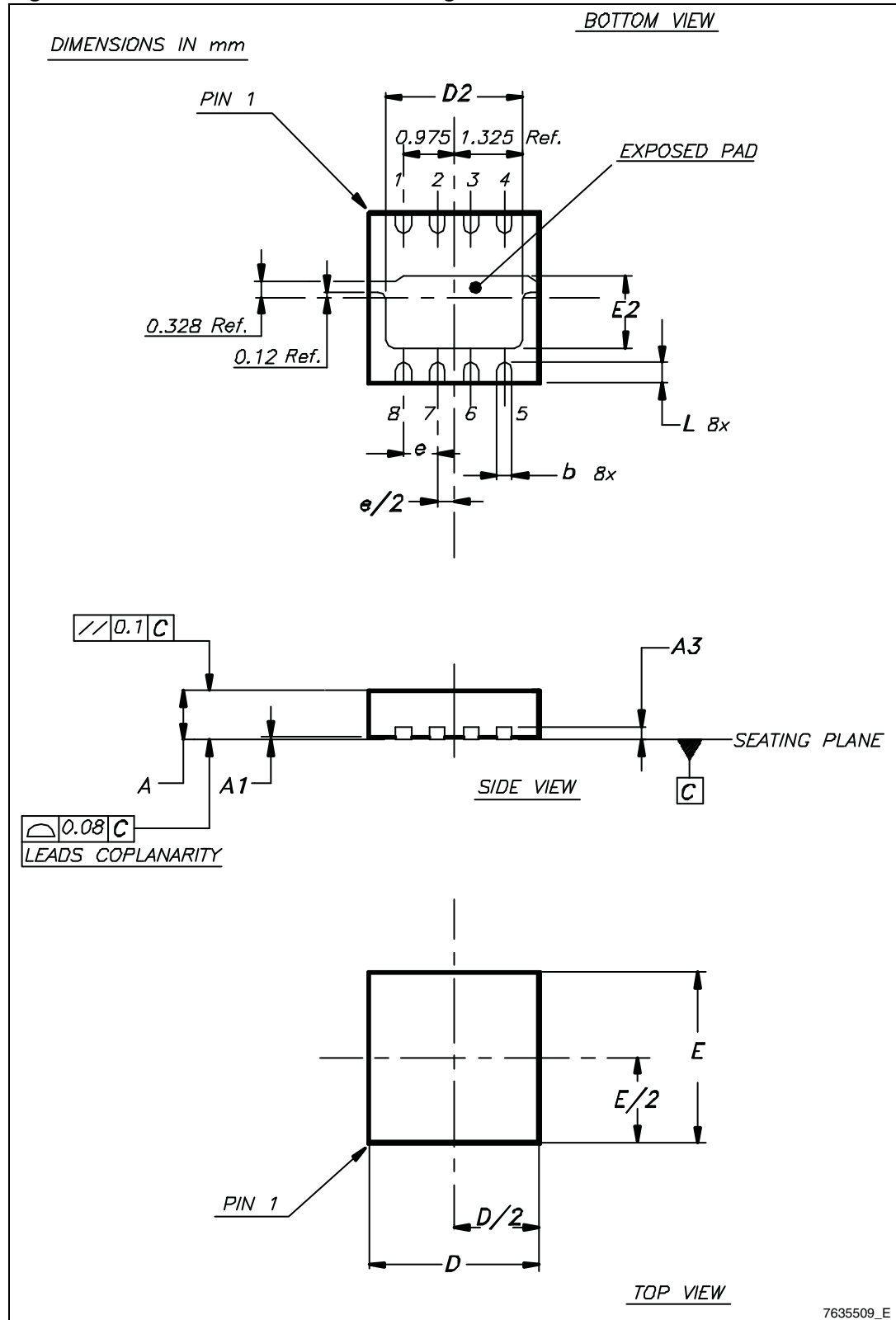
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 9. PowerFLAT™ 3.3 x 3.3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0		0.05
A3		0.20	
b	0.23		0.38
D	3.20	3.30	3.40
D2	2.50		2.75
E	3.20	3.30	3.40
E2	1.25		1.50
e		0.65	
L	0.30		0.50

Figure 19. PowerFLAT™ 3.3 x 3.3 drawing





## 5 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
09-Aug-2011	1	First release.

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